TESD24VS2BT Taiwan Semiconductor

200W, 24V ESD Protection Array

FEATURES

- Small package for use in portable electronics
- Meet IEC61000-4-2(ESD) ±30kV(air) , ±30kV(contact)
- Moisture sensitivity level: level 1, per J-STD-020
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

APPLICATIONS

- High Speed Line: USB 2.0 / VGA/ DVI /SDI /HDMI
- Touch Panel
- Battery Management System
- POE PD

MECHANICAL DATA

- Case: SOT-23
- Molding compound meets UL 94 V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Meet JESD 201 class 1A whisker test
- Weight: 8.70mg (approximately)
- Marking code on the device: W3

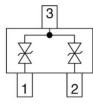
KEY PARAMETERS			
PARAMETER	VALUE	UNIT	
P _{PPM}	200	W	
I _{PP}	3	А	
V _{WM}	24	V	
$V_{\rm C}$ at $I_{\rm PP}$ = 3 A	70	V	
Package	SOT-23		





HALOGEN





ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)				
PARAMETER	SYMBOL	TESD24VS2BT	UNIT	
Rated random recurring peak Impulse power dissipation (tp = 8/20µs waveform)	P _{PPM}	200	W	
Peak impulse current (tp = 8/20µs waveform)	I _{PP}	3	А	
ESD per IEC 61000-4-2 (Air)	N	± 30	kV	
ESD per IEC 61000-4-2 (Contact)	- V _{ESD}	± 30	kV	
Junction temperature range	TJ	-55 to +150	°C	
Storage temperature range	T _{STG}	-55 to +150	°C	



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ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	ТҮР	MAX	UNIT
Reverse breakdown voltage ⁽¹⁾	I _R = 5mA	V _(BR)	25.4	-	-	V
Rated working standoff voltage		V _{WM}	-	-	24	V
Reverse current ⁽¹⁾	V _R = 24V	I _R	-	-	50	nA
Clamping voltage ⁽²⁾	I _{PP} = 1A	Vc	-	-	40	V
Clamping voltage ⁽²⁾	I _{PP} = 3A	Vc	-	-	70	V
Junction capacitance	1MHz, $V_R = 0V$	CJ	-	11	-	pF

Notes:

- 1. Pulse test with PW = 30ms
- 2. $tp = 8/20\mu s$ waveform

ORDERING INFORMATION			
ORDERING CODE	PACKAGE	PACKING	
TESD24VS2BT RFG	SOT-23	3K / 7" Reel	



CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

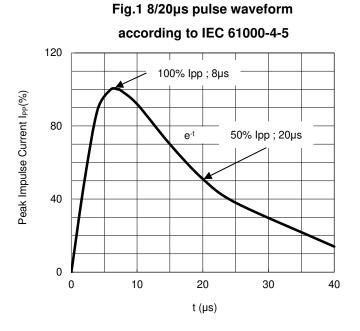


Fig.2 ESD pulse waveform according to IEC 61000-4-2 Peak Impulse Current Ipp(%) -10 t(ns) t_r=0.7ns to 1ns

Reverse Voltage V_R(V)

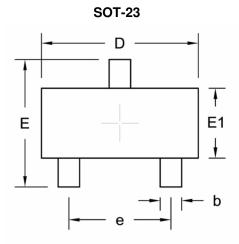
Fig.3 Typical Junction Capacitance

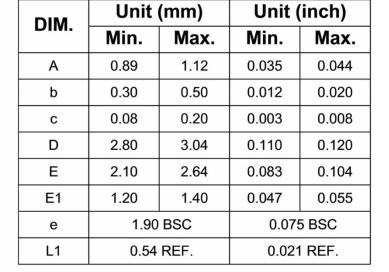
Junction Capacitance CJ(pF)

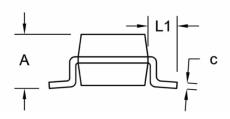
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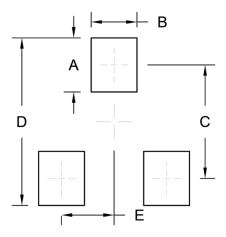
PACKAGE OUTLINE DIMENSIONS







SUGGESTED PAD LAYOUT



Symbol	Unit (mm)	Unit (inch)
A	1.00	0.039
В	0.85	0.033
С	2.10	0.083
D	3.10	0.122
E	0.98	0.039



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